Thermal evolution of silicon carbide electronic bands

E. Cannuccia\textsuperscript{1,2} and A. Gali\textsuperscript{3,4}

\textsuperscript{1}Aix-Marseille Université, Laboratoire de Physique des Interactions Ioniques et Moléculaires (PIIM), UMR CNRS 7345, F-13397 Marseille, France
\textsuperscript{2}Dipartimento di Fisica, Università di Roma “Tor Vergata”, Via della Ricerca Scientifica 1, I-00133 Roma, Italy
\textsuperscript{3}Wigner Research Centre for Physics, Hungarian Academy of Sciences, PO. Box 49, H-1525, Budapest, Hungary
\textsuperscript{4}Department of Atomic Physics, Budapest University of Technology and Economics, Budafoki út 8., H-1111 Budapest, Hungary

Direct observation of temperature dependence of individual bands of semiconductors for a wide temperature region is not straightforward, in particular, for bands farther from the Fermi-level. However, this fundamental property is a prerequisite in understanding the electron-phonon coupling of semiconductors. Here we apply \textit{ab initio} many body perturbation theory to the electron-phonon coupling on hexagonal silicon carbide (SiC) crystals and determine the temperature dependence of the bands. We find a significant electron-phonon renormalization of the band gap at 0 K. Both the conduction and valence bands shift at elevated temperatures exhibiting a different behavior. We compare our theoretical results with the observed thermal evolution of SiC band edges, and discuss our findings in the light of high temperature SiC electronics and defect qubits operation.

Electron-phonon interaction impacts a large variety of fundamental materials properties \cite{1}, from the critical temperature of superconductors to the zero-point renormalization and the temperature dependence of the electronic energy bands, from the electronic band gaps \cite{2,3} to the thermal evolution of the optical spectra and excitonic lifetimes \cite{4,5}. In addition the electron-phonon coupling contributes to the optical absorption and emission in indirect gap semiconductors \cite{6,7,8}, determines the electronic carrier mobility of semiconductors \cite{9}, the carrier relaxation rates \cite{10}, the distortion of band structures and phonon dispersion giving rise to kinks and Kohn anomalies in photoemission \cite{11}.

Direct observation of the temperature evolution of individual bands over a wide region of temperatures is not straightforward. Optical techniques are capable of measuring band gaps, and not the absolute values of the valence band maximum (VBM) and the conduction band minimum (CBM) separately. The interpretation of results from optical techniques is then weakly conclusive. In addition, the indirect band gap nature of some materials prohibits the direct optical transition between VBM and CBM, which turns to be allowed only when phonons assist the optical excitation. Recent attempts used Si 2p core level as a reference to extract the CBM and VBM energy position of Si and hexagonal 6H silicon carbide (SiC) crystals [see Fig. 1(a)] from the onset of soft X-ray absorption spectroscopy (XAS) and soft non-resonant X-ray emission spectroscopy (XES), respectively \cite{12,13}. This method assumes temperature independent core exciton binding energy \cite{14}, which results in a systematically smaller derived band gap than the observed optical band gap, and it may suffer from the accurate observation of the onset energies at elevated temperatures caused by temperature broadening effects. We stress that none of these methods enables the observation of individual bands other than band edges but observation of the temperature dependence of those bands can be an important issue at high temperatures.

It is utterly important to apply \textit{ab initio} many body perturbation theory that can provide valuable insights on the electron-phonon coupling effect in semiconductors by directly describing the temperature dependence of individual bands. This fundamental property has been recently studied typically, only for the band edges and up to room temperature \cite{15,16,17}. We extend these fundamental investigations for high temperatures and beyond band edges for hexagonal 4H and 6H SiC crystals [see Fig. 1(a)]. The choice of these materials was motivated by three points: (i) experimental data is available for the temperature dependence of the gap \cite{18,19,20} and band edges \cite{21}, (ii) SiC based semiconductor devices have been successfully tested at high temperatures (around 800 K) for Venus mission \cite{22}, where deep insight into the electron-phonon interaction of electronic bands has an uttermost importance, and (iii) SiC is a semiconductor platform for hosting hybrid opto-electro-mechanical defect quantum bits \cite{23,24}. These defect quantum bits require very accurate electrical and optical control which depends on the ionization thresholds, i.e., the position of band edges at the operation temperature \cite{25,26}.

In this Letter, we apply density functional theory (DFT) on the electronic structure and phonons in 4H and 6H SiC, and determine the electron-phonon coupling within Heine-Allen-Cardona (HAC) approach. We find a sizable temperature dependent renormalization energy on the electronic structure for both crystals, including the bands farther from the the Fermi-level. As a consequence, both valence and conduction band edges shift with temperature thus affecting the operation of defect qubits at elevated temperatures. We predict that the operation of divacancy qubits in 4H SiC \cite{27} is stabilized at elevated temperatures against bleaching caused by photonization. Furthermore, our \textit{ab initio} results
FIG. 1. (a) Primitive cells of 4H and 6H SiC with \( k \) \((k_1, k_2)\) and \( h \) Si-C bilayers, where \( k \) and \( h \) refers to quasicubic and hexagonal sites. (b) Brillouin-zone of hexagonal SiC polytypes. (c) Sketch of band gap of hexagonal SiC crystals. In 4H SiC, the first \((M_1)\) and second \((M_2)\) conduction bands are close in energy \([36]\). In 6H SiC, the lowest conduction band is very flat along the \( M - L \) line \([37, 38]\), and it should be close to the \( M \) point (see Ref. \([39]\)).

indicate that the conductivity of doped 4H SiC is not much affected at elevated temperatures, thus SiC electrics conforms to high temperature operation.

We perform geometry optimization, electronic structure and phonons calculation, followed by the calculation of electron-phonon matrix elements, and renormalization of the electronic energies as a function of temperature. Density functional theory (DFT) and density functional perturbation theory (DFPT) calculations are carried out using Quantum ESPRESSO 6.1.0 \([40]\) suite. We employ norm-conserving pseudopotentials and the exchange-correlation functional is described by the local density approximation (LDA) with the Perdew-Zunger parametrization \([41]\). We perform in a first step a full optimization (lattice parameters and atomic positions along \( c' \) axis) using 90 Ry as kinetic energy cutoff, \( 18 \times 18 \times 6 \) and \( 18 \times 18 \times 4 \) k-meshes for 4H and 6H SiC crystals, respectively. The phonon frequencies are obtained with the same kinetic energy cutoff on a \( 10 \times 10 \times 3 \) and \( 10 \times 10 \times 2 \) q-meshes, respectively, and then interpolated along the \( q \)-path connecting \( \Gamma - K - M - \Gamma - A \) high symmetry points.

The same k-point sampling of the Brillouin-zone and cutoff are used to calculate the phonon frequencies and the derivatives of the self-consistent Kohn-Sham potential with respect to the atomic displacements needed to evaluate the electron-phonon coupling matrix elements. Unoccupied bands as many as five times the number of the occupied ones are taken into account for 4H SiC. On the other hand for 6H we are bound to use 96 unoccupied bands (four times the number of occupied ones) because of technicalities in the applied algorithms and computational capacity. We note that this affects the convergence of 6H SiC results as discussed in Ref. \([39]\).

We will present the extrapolated convergent values for 6H SiC that are estimated from the convergence study of 4H SiC results. Many-body perturbation theory is used to get the temperature dependent correction of the bare electronic energies, owing to the phonon field perturbation, within HAC approach.

The key issue of this study is the calculation of the temperature dependent correction to the electronic state \(| n k \rangle\), with energy \( \varepsilon_{n k} \) due to the electron-phonon interaction. The electron-phonon interaction is treated perturbatively \([42, 43]\) within the Heine-Allen-Cardona (HAC) approach by considering the first- and second-order Taylor expansion of the self-consistent potential \( V_{\text{scf}}(\mathbf{r}) \) \([44]\) in the nuclear displacements \( \mathbf{u} \) with respect to the equilibrium positions \( \mathbf{R} \). Standard perturbation theory is then applied. The first order Taylor expansion of \( V_{\text{scf}}(\mathbf{r}) \) is treated within the second–order perturbation theory, while the second order Taylor expansion is treated within the first-order perturbation theory. The corresponding temperature dependent energy shift of the electronic state is then composed of Fan term

\[
\Delta \varepsilon_{n k}^{\text{Fan}}(T) = \sum_{\mathbf{q} \lambda} \frac{1}{N} \sum_{n'} \frac{|g_{n' n k}^{\lambda}|^2}{\varepsilon_{n k} - \varepsilon_{n' k'}} \times (2B(\omega_{q \lambda}) + 1),
\]

where \( N \) is the number of \( \mathbf{q} \) points, while \( |g_{n' n k}^{\lambda}|^2 \) are the electron-phonon matrix elements for the scattering between the electronic states \(| n k \rangle\) and \(| n' k + \mathbf{q} \rangle\) via the phonon \( \mathbf{q} \lambda \), defined as

\[
g_{n' n k}^{\mathbf{q} \lambda} = \sum_{s \alpha} (2M_s \omega_{\mathbf{q} \lambda})^{-1/2} e^{i \mathbf{q} \cdot \tau_s} \times \langle n' k + \mathbf{q} | \frac{\partial V_{\text{scf}}(\mathbf{r})}{\partial R_{\alpha}} | n k \rangle \xi_{\alpha}(\mathbf{q} \lambda | s),
\]

and the DW contribution

\[
\Delta \varepsilon_{n k}^{\text{DW}}(T) = -\frac{1}{2} \sum_{\mathbf{q} \lambda} \sum_{n' n} \frac{\lambda_{n' n k}^{\mathbf{q} \lambda}}{\varepsilon_{n k} - \varepsilon_{n' k}} \times (2B(\omega_{q \lambda}) + 1),
\]

where \( \lambda_{n' n k}^{\mathbf{q} \lambda} \) is an expression written in terms of \( \nabla V_{\text{scf}} \) and obtained by imposing the translational invariance of \( \Delta \varepsilon_{n k} \) when all atoms in the crystal are displaced of the same amount from their equilibrium positions.

In Eqs. \([45,46]\) \( \omega_{q \lambda} \) are the phonon frequencies, calculated ab-initio using DFPT, \( M_s \) is the atomic mass, \( \tau_s \) is the position of the atom displacement in the unit cell and \( \xi_{\alpha}(\mathbf{q} \lambda) \) are the components of the phonon polarization vectors corresponding to the phonon momentum \( \mathbf{q} \) and branch \( \lambda \).
The key quantity in Eqs. (1) and (3) is the Bose function distribution $B(\omega_{q\lambda}) = (e^{\frac{\omega_{q\lambda}}{k_B T}} - 1)^{-1}$. When the temperature ($T$) vanishes the energy correction does not vanish due to the $(2B(\omega_{q\lambda}) + 1)$ factor yielding the zero-point motion renormalization (ZPMR).

Since the thermal expansion minutely increases the lattice constants of hexagonal SiC [15], the thermal evolution of the band structure and of the electronic gap will be caused mainly by the electron-phonon interaction. We assess first the HAC approach to describe the thermal evolution of $4H$ and $6H$ SiC indirect band gaps. At $T = 0K$, we found 0.17 eV and 0.14 eV for $4H$ and $6H$ SiC, respectively as of the indirect electronic band gaps. These values are about 5% of the indirect electronic band gaps, revealing an intermediate ZPMR value in between bulk silicon and diamond [3, 40]. The calculated temperature dependence of the indirect band gap can be compared to that of the observed optical gap of SiC crystals [19, 20, 17]. In Fig. 2(a) and 2(b) the calculated temperature-dependent indirect band gaps are aligned to the experimental data at $T = 0K$ (see Ref. 39 about the electron quasiparticle correction), in order to readily compare the temperature evolution. We find an excellent agreement with the experimental data as derived from the optical gaps for a wide range of temperatures, which allows us to predict a shrinking of the electronic gap of about 0.32 eV ($4H$ SiC) and 0.30 eV ($6H$ SiC) at $T = 800K$.

Next, we study the temperature dependence of the individual bands. In particular, we focus on the valence band maximum (VBM) and conduction band minimum (CBM) [see Figs. 2(c) and (d)], whose difference provides the indirect band gap plotted in Figs. 2(a) and (b). Since VBM and CBM do not occur at the same point of the BZ, they have different symmetries and they interact differently with phonons. For $4H$ and $6H$ SiC, in fact, we predict an asymmetry in the band gap closing, where the contribution from the VBM is larger, respectively ~63% and ~58% of the total band gap shrinking. Here, we stress that the latter result has been estimated. We used the converged data set for $4H$ SiC (see Fig. S3 of Ref. 39) to extrapolate convergent data for $6H$ SiC because an explicit convergent calculation is computationally prohibitive as explained in Ref. 39 (see also Fig. S3). In Fig. 2(d) we report the temperature dependent XAS and XES spectra which depict respectively the CBM and VBM behaviour in $6H$ SiC [17]. Both XAS and XES experimental data have been shifted to match the temperature evolution of CBM and VBM. We find a very good agreement with XAS derived data. The XES one also agrees with the estimated converged data set. Our theory well supports the observed temperature evolution of the indirect band gap of $4H$ SiC.

The nature of the electron-phonon coupling induced renormalization in $4H$ and $6H$ SiC can be analyzed in the light of plotted Eliashberg function (Fig. 3), where the separate contribution of Fan and DW terms is highlighted. The VBM states are mostly coupled to the optical phonons (LO and TO) starting from 780 cm$^{-1}$. In this phonon frequency energy range both Fan and DW have a significant weight in the energy renormalization; while they almost cancel each other in the acoustic phonon frequency range. On the other hand, the CBM states (here called $M_1$) and the second lowest conduction band (here called $M_2$) also couple to acoustic phonons already from 220 cm$^{-1}$. Most of the contribution is given by the Fan term, which dominates all over the whole phonon frequency range. The difference between the CBM and VBM Eliashberg functions, being negative, is strictly related to the temperature dependence of the fundamental band gap shown in Fig. 2. The square modulus of VBM wavefunction shows that the charge density is mainly localized on the Si-C bond of the hexagonal Si-C layer (off-axis Si-C bonds). The coupling with planar optic modes, as highlighted by the Eliashberg functions, is then justified, as these vibrations change the length of the interatomic bonds in which the charge density associated with the VBM resides [40]. The CBM states are localized in the interstitial places of $4H$ SiC lattice [43], in contrast to the bond localized charge density of the VBM. The coupling with optical modes slightly loses weight and it is transferred to acoustic modes.

We observe now that the calculated lowest energy conduction bands of $4H$ SiC labeled as $M_1$ and $M_2$ are quite close in energy (see Tab. SI in Ref. 39). According to a recent measurement, the energy separation of the two lowest conduction bands at $M$ point of the Brillouin-zone is 144±2 meV at 2 K [36]. If these two bands crossed at elevated temperatures then this could seriously affect the $n$-type conductivity of the SiC based electronic devices. We find that the energy separation between $M_1$ and $M_2$ only reduces by 5 meV (< 5%) going from 0 K to 800 K temperatures (see Fig. S4 in Ref. 39) because both $M_1$ and $M_2$ bands shift downwards with increasing temperatures. We note that similar properties are found in $6H$ SiC (see Ref. 39). The calculated effective masses of the $M_1$ and $M_2$ bands (see Table SIII in Ref. 39) imply that the conductivity of the $M_2$ band is smaller than that of the $M_1$ band except in the $K - M$ direction. However, the overall conductivity still increases (see Fig. S6 in Ref. 39) because of a larger number of typical nitrogen donors ionization at $k$ and $h$ sites at 120 and 60 meV [49], respectively, with increasing temperatures. This paves the way for space agencies to employ $4H$ SiC based integrated circuits to probe the surface of Venus, where the temperature is $\approx$730 K [21].

Our fundamental study has implications on the quantum bits hosted by $4H$ SiC such as neutral divacancies [23, 24]. Divacancy qubits are initialized and readout by optically detected magnetic resonance (ODMR) [24], where illumination at about 1.17 eV used in this pro-
FIG. 2. Calculated thermal evolution of indirect band gaps in the temperature range $0 - 800$ K for (a) 4H and $0 - 1000$ K for (b) 6H SiC. The calculated curves are aligned to the experimental data at $T = 0$K. For 6H an extrapolation at 150 bands (red squares: estimated convergent data) is given for comparison. The experimental data (green crosses) of the optical gaps are taken from Refs. [19-20] and [47]. In 6H SiC case, the CBM$_{XAS}$-VBM$_{XES}$ band gap is determined by the experimental XAS and XES data points as a function of temperature (Ref. [17]). The optical band gap has been extracted from RIXS spectra, with correction of the core-hole exciton binding energy included. Thermal evolution of calculated VBM and CBM of (c) 4H SiC and (d) 6H SiC, where the latter is compared to the XAS and XES measurements (Ref. [17] rescaled of 99.5 eV and 98.65 eV, respectively, in order to match the temperature evolution of CBM and VBM.

The qubit state can be restored by applying $\sim 1.3$ eV optical excitation [33-35], where the nature of the dark state was debated in the literature [33, 34, 50]. According to one of the most recent study [35], the dark state can be identified as the negative charge state of divacancies where optical excitation at $\sim 1.25$ eV is the threshold of photoionization of the electron from the in-gap defect level to the conduction band edge at cryogenic temperatures. The coherent control of defect spins in 4H SiC can be achieved even at high temperatures up to 600 K [31] paving the way for SiC-based broad-temperature-range quantum sensing such as magnetic and temperature sensing. As the typical excitation energy of the qubit and the threshold for photoionization of the dark state is close in energy, the temperature dependent band edge and photoionization energies can seriously affect the stability of the charge state of divacancies, i.e., the operation of divacancy qubits. We find that the CBM of 4H SiC shifts down by 0.1 eV going from cryogenic temperatures up to 600 K. This implies that the threshold for photoionization reduces $\sim 0.1$ eV. We conclude that high temperature operation of 4H SiC divacancy qubits would be stable against photoionization.
Our study on the fundamental properties of 4H and 6H SiC revealed that the nearest lowest-energy conduction bands do not cross at elevated temperatures. We also found that the shift of both the valence bands and conduction bands contributes to the decrease of the fundamental indirect band gap of SiC at increasing temperatures, and supports the interpretation of temperature dependent optical gaps. We conclude that SiC exhibits favorable properties for hosting electronic devices at extreme high temperatures operation which is important for next generation sensors and electronics in space missions. Our study has an impact on quantum technology applications too, and serves as a template for similar studies in other semiconductors.

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Supplemental Materials for the paper entitled
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Description of the hexagonal silicon carbide crystals

Silicon carbide (SiC) has over 250 polytypes which share the same hexagonal lattice in the basal plane and different stacking sequences of Si-C bilayers perpendicular to the basal plane. The most important polytypes are the so-called 4H and 6H SiC as shown in Fig. 1(a) and Fig. 1(a) in the main text. They consist of 4 and 6 Si-C double layers having a close-packed hexagonal arrangement. There are three types of hexagonal close packing (A, B and C) in arranging the Si-C double atomic layers. In 4H and 6H the stacking sequences are ABCB|ABCB|… and ABCACB|ABCACB|…, respectively. Each atom (Si or C) has a local quasicubic (k) or hexagonal (h) environment with respect to the immediate neighbors. The experimental lattice constants are a = 3.08 Å with c = 10.08 Å [52] and a = 3.08 Å with c = 15.12 Å [52] for 4H and 6H SiC, respectively, and the ideal values for the internal parameters follow from the space group symmetry C6v [37].

Electronic structure of hexagonal silicon carbide crystals

We applied density functional theory (DFT) within local density approximation (LDA) as reported in the main text. The calculation of the phonon dispersion curves required the optimization of the lattice constants. This results into a = 3.07 Å with c = 10.0 Å [52] and a = 3.07 Å with c = 15.0 Å [52] for 4H and 6H SiC, respectively, that are close to the experimental values. The optimized internal parameters remain close to the ideal ones [37].

4H and 6H-SiC are indirect semiconductors with a relatively large band gaps at room temperature, 3.26 and 3.02 eV, respectively [53]. The calculated electronic band structure are shown in Fig. 1(c) and (d) versus high symmetry lines A-Γ-M-L-A within the Brillouin-zone (BZ) of the hexagonal system. The overall features show the agreement with previous calculations [37, 54, 55]. The top of the occupied valence-bands states is located at Γ in both polytypes. As reported by [37, 38] the exact position of conduction band minimum depends on the details of the calculation, the ratio c/a of the hexagonal lattice constants, as well as the atomic positions inside the hexagonal unit cell. We find the conduction band minimum at M for 4H SiC and at about 0.5 M – L for 6H-SiC. However, the lowest conduction band is rather flat between L and M in 6H-SiC case. For this reason, we assume that the bottom of the conduction band occurs at the M point of the BZ, yielding just a minor error in the calculated LDA fundamental gap for 6H-SiC. Moreover,

FIG. 3. Generalized electron-phonon Eliashberg function at 0K for 4H SiC (a) valence band maximum (Γ-point), (b) first conduction band minimum (M1-point) and (c) second conduction band minimum (M2-point). Fan and Debye-Waller (DW) contributions are shown separately with dashed and solid lines, respectively.
we observe that at the CBM two bands are very close in energy. We will label them in the follow as $M_1$ and $M_2$.

At DFT-LDA level we obtain 2.25 eV for 4H SiC and 2.04 eV for 6H SiC, about 1.0 eV lower than the corresponding measured values, and in agreement with other theoretical works [57, 58]. The discrepancy in the absolute value of the indirect band gaps comes from the well-known self-interaction error of the LDA but the curvature of the individual bands are well reproduced by this approximation. As a consequence, the effective masses of the electrons, i.e., the second derivatives of the energies around the $M$ point for the conduction band minimum, can be accurately calculated by DFT-LDA.

Quasiparticle correction in the electronic structure of hexagonal silicon carbides

Assuming DFT-LDA orbitals as a good approximation to the quasi-particle (QP) orbitals, the first-order correction to the Kohn-Sham eigenenergies is obtained within a single iteration of Hedin’s GW approximation [56, 57]. For 6H-SiC, the exact position of the conduction band minimum (CBM) on the $L - M$ line has been under discussion [37, 38, 54]. Wenzien et al. [55] found a tendency of CBM of 6H-SiC to move towards $M$ point after the inclusion of QP effects. They used a simplified GW method, meaning a model dielectric function and an approximate treatment of the local field effects. Ummels et al. [58] performed GW calculations for the 2H, 4H, and 6H SiC polytypes using the Engel and Farid plasmon-pole model for the description of the energy dependence of the screened interaction. They obtained $G_0W_0$ indirect band gaps listed in Table II. We calculated the opening of the indirect gap due to QP effects adopting the Godby-Needs plasmon-pole model [50, 51, 60, 61], obtaining 0.92 eV QP-level correction for both 4H and 6H SiC. We used $18 \times 16 \times 6$ and $16 \times 16 \times 3$ k-point sets for 4H and 6H SiC, respectively, with 200 bands in the numerically convergent GW calculations. Our correction results to be lower with respect to those calculated by Ummels et al. [58]. This is due to the different plasmon pole model used. Godby-Needs plasmon-pole model best reproduces the model-free contour deformation (CD) results [62], when other PP models are applied the gap obtained is significantly higher and in particular Engel and Farid PPM gives for ZnO a GW correction 0.3-0.4 eV larger than the CD one [63].

Our LDA energies for the highest valence band and the lowest conduction bands at $\Gamma$ and $M$ points are listed in Table I together with previous GW gaps [58] and experimental data [19]. The experimental data comes from optical measurements in which the exciton binding energies should be accounted for comparison to the calculated electronic band gaps. These binding energies are experimentally found to be 0.020 eV and 0.078 eV in 4H and 6H SiC [64, 65], respectively, i.e., which are smaller than the expected accuracy of the GW calculations.

In our study, we have to rely on the DFT-LDA geometries as we have to calculate phonon bands which assumes to stay close to the global energy minimum of the adiabatic potential energy surface. Our GW calculations justify to apply a simple scissor correction on the DFT-LDA band gaps, in order to reproduce the experimental ones.

Phonons of hexagonal silicon carbides

In view of the calculation of the temperature dependent renormalization of the electronic gap, the phonon dispersion curve is an essential input for phonon-related properties. Besides the fact that the phonon dispersion curve reflects the structure of a material and its symmetries [66], phonon spectra are one of the key ingredients that help in understanding the coupling between electrons and lattice vibrations. Symmetry analysis shows that phonon modes can be decomposed into $N(A_1 \oplus E_1 \oplus E_2)$ modes, where $N = 4, 6$ for 4H SiC and 6H SiC, respectively. Whose modes $A_1 \oplus E_1$ are acoustic and $(N-1)A_1 \oplus NB_1 \oplus (N-1)E_1 \oplus NE_2$ are optic modes. Except for $B_1$ modes which are infrared and Raman forbidden, all the other are Raman active modes. Out of them $A_1$ and $E_1$ modes are also infrared active.

The calculated phonon dispersion curves are shown in Fig. 5. Table II reports the theoretical and experimental phonon frequencies at $\Gamma$ point for 4H- and 6H-SiC. All the available experimental modes were readily assigned. The phonon modes with longer wavelength are divided into axial or basal plane modes, depending if the atoms displace parallel or perpendicular to the $c$-axis, as explained in Ref. 67. The planar modes consist of Raman and IR active $E_1$ modes and Raman active $E_2$ modes. The axial modes consist of Raman active $A_1$ and Raman inactive $B_1$ modes. Our vibrational frequencies at $\Gamma$ point are in excellent agreement with previously published calculations and with experimental phonon dispersion curves obtained by infrared and Raman spectroscopies [68, 72], being the average error smaller than 4 cm$^{-1}$. This supports our choice of using DFT-LDA eigenenergies and DFPT-LDA phonon frequencies as key ingredients for the calculation of the electron-phonon interaction.

Additional data on the calculated electron-phonon interaction

This section provides details about the convergence of the temperature dependent electron-phonon coupling of the valence bands as well as the the calculated temperature shifts for the two lowest energy conduction bands.
around $M$ point.

We find that the calculated temperature shifts of the valence bands depends on the number of conduction bands used in the calculation of electron-phonon coupling whereas the temperature shifts of the conduction bands converge much faster with the number of conduction bands. As can be inferred in Fig. 6(a), the calculated temperature shifts of the conduction bands used in the calculation of electron-phonon coupling for $4H$ SiC, as the 90 bands and 100 bands data are practically identical. This corresponds to about 6× of the number of valence bands (16 bands without core electrons). As a consequence, the convergent number of bands should be around 150 for $6H$ SiC that has 24 valence bands. However, it is technically prohibitive to carry out such calculations for $6H$ SiC. Thus, we carried out electron-phonon coupling calculations with non-converged 120 bands, which is only 5× of the number of valence bands. We estimated the converged data by taking the difference in the calculated 80 bands data (5× of the number of valence bands in $4H$ SiC) and the convergent 100 bands data of $4H$ SiC. Then we extrapolated the convergent 150 bands numerical data by these differences at the given temperature in $6H$ SiC.

Next we turn to the calculated temperature shifts for the two lowest energy conduction bands around $M$ point. We found an energy separation of 89 meV at DFT level between the two lowest conduction bands of $4H$-SiC, as reported in Table I. QP corrections shift down the second conduction band with respect to the first one of 3 meV. The final inclusion of the electron-phonon interaction leads to a positive zero point energy correction of 2 meV and 6 meV at 800 K. For $6H$ SiC the energy separation is 170 meV at DFT level, it increases up to 180 meV by the inclusion of QP effects, and then it gets to 183 meV with zero point energy correction. In Fig. 3 the generalized electron-phonon Eliashberg function in $6H$ SiC are shown. As discussed for $4H$ SiC in the main manuscript, the contribution of the different phonon mode groups to the electron-phonon renormalization of the band gaps can be directly deduced.

**Additional data about conductivity of electrons in $4H$ SiC**

In extrinsic semiconductors, containing donor impurities, the presence of donor levels shifts the Fermi level from the middle of the energy gap toward the edge of the conduction band. Let us define the ionization temperature of the donor levels $T_d$ as

$$k_B T_d = \epsilon_d$$

where $\epsilon_d$ is the binding energy of the donor levels, $k_B$ is the Boltzmann constant and the density $N_d$ of donor impurities is supposed to be uniform in the sample. In very low temperature regime, $T \ll T_d$ we expect that all the donor levels are occupied and the chemical potential must be located in the energy range $E_d < \mu(T) < E_c$, where $E_d$ is the donor level and $E_c$ is the lowest conduction band position. In this temperature range the temperature dependence of carrier conductivity is given by Refs. 73 and 74

$$\sigma_{\text{imp}} \sim \left( N_c(T) \frac{N_d}{2} e^{-\epsilon_d/2k_B T} \right) \cdot \frac{e^2}{m_e^*} T^{3/2},$$

being inversely proportional to the effective mass of the electron, which is the second derivative of the given conduction band along a given direction in the Brillouin zone. The effective masses in the second conduction band ($M_2$) is generally greater (except along $K - M$ line) than in the first conduction band ($M_1$) (see Table III). $N_d$ is the donor impurities density $\sim 10^{18} - 10^{19} \text{cm}^{-3}$ and electronic charge $e = 1.6 \times 10^{-19} \text{C}$. The carrier conductivity for binding energy donor levels equal to 120 meV in $4H$ SiC is represented in Fig. 9.


FIG. 4. (a) Primitive cells of $4H$ and $6H$ SiC with $k$ ($k_1$, $k_2$) and $h$ Si-C bilayers where $k$ and $h$ refer to quasicubic and hexagonal sites. (b) Brillouin-zone of hexagonal SiC polytypes. (c) Calculated LDA band structure of $4H$ SiC. The valence band maximum (VBM) is at the $\Gamma$ point, whereas the conduction band minimum (CBM) is at the $M$ point. (d) Calculated LDA band structure of $6H$ SiC. The first conduction band is very flat in the $L-M$ line [37, 38]. While the VBM is still at $\Gamma$ point, we find the CBM in between point $L$ and $M$. The VBM energies are aligned to zero, and the band gap is highlighted by yellow color (shadowed).
FIG. 5. Phonon band dispersion of $4H$ and $6H$ SiC as obtained within Density Functional Perturbation Theory (DFPT).
TABLE II. 4H- and 6H-SiC optic (Opt.) and low energy acoustic (Ac.) phonon frequencies at Γ point (in cm$^{-1}$) either in the basal plane (B.) or along c-axis (Ax.) and their corresponding irreducible representation (Irrep). $B_1$ modes are Raman and infrared (IR) forbidden. There are modes for both compounds that were not observed (N.O.).

<table>
<thead>
<tr>
<th>Irrep</th>
<th>DFPT-LDA freq.</th>
<th>Exp. Raman</th>
<th>Exp. IR reflectivity</th>
<th>Branch</th>
</tr>
</thead>
<tbody>
<tr>
<td>$E_2$</td>
<td>192.3</td>
<td>196.0</td>
<td>-</td>
<td>B.Ac.</td>
</tr>
<tr>
<td>$E_2$</td>
<td>200.3</td>
<td>204.0</td>
<td>-</td>
<td>B.Ac.</td>
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<tr>
<td>$E_1$</td>
<td>259.2</td>
<td>266.0</td>
<td>-</td>
<td>B.Ac.</td>
</tr>
<tr>
<td>$B_1$</td>
<td>401.1</td>
<td>-</td>
<td>-</td>
<td>Ax.Ac.</td>
</tr>
<tr>
<td>$B_1$</td>
<td>409.2</td>
<td>-</td>
<td>-</td>
<td>Ax.Ac.</td>
</tr>
<tr>
<td>$A_1$</td>
<td>608</td>
<td>610.0</td>
<td>610.5</td>
<td>Ax.Ac.</td>
</tr>
<tr>
<td>$E_1$</td>
<td>763.9</td>
<td>N.O.</td>
<td>B.Opt.</td>
<td></td>
</tr>
<tr>
<td>$E_2$</td>
<td>771.4</td>
<td>N.O.</td>
<td>B.Opt.</td>
<td></td>
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<tr>
<td>$E_2$</td>
<td>779.7</td>
<td>776.0</td>
<td>-</td>
<td>B.Opt.</td>
</tr>
<tr>
<td>$E_1$</td>
<td>790.2</td>
<td>797</td>
<td>-</td>
<td>B.Opt.</td>
</tr>
<tr>
<td>$A_1$</td>
<td>838.7</td>
<td>838</td>
<td>839</td>
<td>Ax.Opt.</td>
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<tr>
<td>$B_1$</td>
<td>910.6</td>
<td>-</td>
<td>-</td>
<td>Ax.Opt.</td>
</tr>
<tr>
<td>$B_1$</td>
<td>920.1</td>
<td>-</td>
<td>-</td>
<td>Ax.Opt.</td>
</tr>
<tr>
<td>$A_1$</td>
<td>958.8</td>
<td>964</td>
<td>-</td>
<td>Ax.Opt.</td>
</tr>
</tbody>
</table>

<table>
<thead>
<tr>
<th>Irrep</th>
<th>DFPT-LDA freq.</th>
<th>Exp. Raman</th>
<th>Exp. IR reflectivity</th>
<th>Branch</th>
</tr>
</thead>
<tbody>
<tr>
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<td>145.0</td>
<td>-</td>
<td>B.Ac.</td>
</tr>
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<td>149.0</td>
<td>-</td>
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<td>235.2</td>
<td>241.0</td>
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<td>-</td>
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<td>$B_1$</td>
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<td>504</td>
<td>-</td>
<td>Ax.Ac.</td>
</tr>
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<td>508</td>
<td>-</td>
<td>Ax.Ac.</td>
</tr>
<tr>
<td>$B_1$</td>
<td>610.5</td>
<td>-</td>
<td>-</td>
<td>Ax.Ac.</td>
</tr>
<tr>
<td>$E_2$</td>
<td>763.1</td>
<td>766</td>
<td>-</td>
<td>B.Opt.</td>
</tr>
<tr>
<td>$E_1$</td>
<td>765.7</td>
<td>769</td>
<td>-</td>
<td>B.Opt.</td>
</tr>
<tr>
<td>$E_1$</td>
<td>773.3</td>
<td>777</td>
<td>-</td>
<td>B.Opt.</td>
</tr>
<tr>
<td>$E_2$</td>
<td>782.0</td>
<td>N.O.</td>
<td>-</td>
<td>B.Opt.</td>
</tr>
<tr>
<td>$E_2$</td>
<td>783.2</td>
<td>788</td>
<td>-</td>
<td>B.Opt.</td>
</tr>
<tr>
<td>$E_1$</td>
<td>789.5</td>
<td>797</td>
<td>789</td>
<td>B.Opt.</td>
</tr>
<tr>
<td>$B_1$</td>
<td>837.9</td>
<td>-</td>
<td>-</td>
<td>Ax.Opt.</td>
</tr>
<tr>
<td>$A_1$</td>
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<td>N.O.</td>
<td>884</td>
<td>Ax.Opt.</td>
</tr>
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<td>$A_1$</td>
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<td>889</td>
<td>889</td>
<td>Ax.Opt.</td>
</tr>
<tr>
<td>$B_1$</td>
<td>937.1</td>
<td>-</td>
<td>-</td>
<td>Ax.Opt.</td>
</tr>
<tr>
<td>$B_1$</td>
<td>944.8</td>
<td>-</td>
<td>-</td>
<td>Ax.Opt.</td>
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<tr>
<td>$A_1$</td>
<td>960.1</td>
<td>964</td>
<td>-</td>
<td>Ax.Opt.</td>
</tr>
</tbody>
</table>

$^a$ Refs. [68] and [71]
$^b$ Ref. [72]
$^c$ Ref. [69]
$^d$ Ref. [72]
FIG. 6. Calculated temperature shifts of the indirect energy gap and of individual bands as a function of the number of conduction bands in the calculation of electron-phonon coupling. (a) and (c) 4H SiC for the temperature range 0 – 800 K, the effect of the growing number of unoccupied bands on the thermal evolution of band edges is shown. (b) and (d) 6H SiC for the temperature range 0 – 1000 K, with explicit calculation of 120 bands and extrapolated values at 150 bands based on the 4H SiC data in (a). The calculated curves are aligned to the experimental data at T = 0K. The experimental data (green crosses) of the optical gaps are taken from Refs. 19, 20, and 47. In 6H SiC case, the CBM_XAS-VBM_XES band gap is determined by the experimental XAS and XES data points as a function of temperature (Ref. 17). The optical band gap has been extracted from RIXS spectra, with correction of the core-hole exciton binding energy included.

TABLE III. Effective masses of electrons in the conduction band minima in units of free electron mass \( m_0 \). Experimental data (exp.) are taken from Ref. 75.

<table>
<thead>
<tr>
<th>Effective mass</th>
<th>direction</th>
<th>( M_1 )</th>
<th>( M_1 ) (exp.)</th>
<th>( M_2 )</th>
</tr>
</thead>
<tbody>
<tr>
<td>( m_{\perp} )</td>
<td>( m_{\Gamma M} )</td>
<td>0.48</td>
<td>0.42</td>
<td>0.67</td>
</tr>
<tr>
<td>( m_{</td>
<td></td>
<td>} )</td>
<td>( m_{LM} )</td>
<td>0.27</td>
</tr>
<tr>
<td>( m_{\perp} )</td>
<td>( m_{KM} )</td>
<td>0.28</td>
<td>0.16</td>
<td></td>
</tr>
</tbody>
</table>
FIG. 7. Temperature dependent energy gap between $M_1$ and $M_2$ conduction bands for $4H$ SiC (left panel) and $6H$ SiC (right panel) as obtained starting from DFT-LDA and QP corrected band structure. The experimental splitting at 2 K is about 144 meV in $4H$ SiC (Ref. 36).
FIG. 8. Generalized electron-phonon Eliashberg function at 0 K for 6H SiC (a) valence band maximum (Γ-point), (b) close to the first conduction band minimum (M₁-point) and (c) close to the second conduction band minimum (M₂-point). Fan and Debye-Waller (DW) contributions are shown separately with dashed and solid lines, respectively.
FIG. 9. Carrier Conductivity for 120 meV donor level for the first and second bands of 4H SiC and long the three directions Γ-M, Γ-L, K-M.